

"Low Side Chopper" IGBT SOT-227 (Ultrafast IGBT), 50 A


SOT-227

FEATURES

- NPT Generation V IGBT technology
- Square RBSOA
- HEXFRED® clamping diode
- Positive $V_{CE(on)}$ temperature coefficient
- Fully isolated package
- Speed 8 kHz to 60 kHz
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRODUCT SUMMARY

V_{CES}	1200 V
I_C DC	50 A at 92 °C
$V_{CE(on)}$ typical at 50 A, 25 °C	3.22 V
Package	SOT-227
Circuit	Chopper low side switch

BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting on heatsink
- Plug-in compatible with other SOT-227 packages
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	84	A
		$T_C = 80\text{ °C}$	57	
Pulsed collector current	I_{CM}		150	
Clamped inductive load current	I_{LM}		150	
Diode continuous forward current	I_F	$T_C = 25\text{ °C}$	76	
		$T_C = 80\text{ °C}$	52	
Gate to emitter voltage	V_{GE}		± 20	V
Power dissipation, IGBT	P_D	$T_C = 25\text{ °C}$	431	W
		$T_C = 80\text{ °C}$	242	
Power dissipation, diode	P_D	$T_C = 25\text{ °C}$	278	
		$T_C = 80\text{ °C}$	156	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CE)}$	$V_{GE} = 0\text{ V}$, $I_C = 1\text{ mA}$	1200	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$	-	2.46	-	
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$	-	3.22	2.80	
		$V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.84	3.60	
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	3.78	3.00	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 500\text{ }\mu\text{A}$	4	5	4	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$ ($25\text{ }^{\circ}\text{C}$ to $125\text{ }^{\circ}\text{C}$)	-	- 10	-	mV/ $^{\circ}\text{C}$
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 1200\text{ V}$	-	6	50	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 1200\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	0.7	2.0	mA
Diode reverse breakdown voltage	V_{BR}	$I_R = 1\text{ mA}$	1200	-	-	V
Diode forward voltage drop	V_{FM}	$I_C = 25\text{ A}$, $V_{GE} = 0\text{ V}$	-	1.99	2.42	V
		$I_C = 50\text{ A}$, $V_{GE} = 0\text{ V}$	-	2.53	3.00	
		$I_C = 25\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	1.96	2.30	
		$I_C = 50\text{ A}$, $V_{GE} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	2.66	3.08	
Diode reverse leakage current	I_{RM}	$V_R = V_R$ rated	-	4	50	μA
		$T_J = 125\text{ }^{\circ}\text{C}$, $V_R = V_R$ rated	-	0.6	3.0	mA
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 200	nA

SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q _g	I _C = 50 A, V _{CC} = 600 V, V _{GE} = 15 V		-	400	-	nC	
Gate to emitter charge (turn-on)	Q _{ge}			-	43	-		
Gate to collector charge (turn-on)	Q _{gc}			-	187	-		
Turn-on switching loss	E _{on}	I _C = 50 A, V _{CC} = 600 V, V _{GE} = 15 V, R _g = 5 Ω, L = 500 μH, T _J = 25 °C	Energy losses include tail and diode recovery (see fig. 18)	-	2.72	-	mJ	
Turn-off switching loss	E _{off}			-	1.11	-		
Total switching loss	E _{tot}			-	3.83	-		
Turn-on switching loss	E _{on}	I _C = 50 A, V _{CC} = 600 V, V _{GE} = 15 V, R _g = 5 Ω, L = 500 μH, T _J = 125 °C		-	3.94	-		
Turn-off switching loss	E _{off}			-	2.31	-		
Total switching loss	E _{tot}			-	6.25	-		
Turn-on delay time	t _{d(on)}			-	191	-	ns	
Rise time	t _r	-		53	-			
Turn-off delay time	t _{d(off)}	-		223	-			
Fall time	t _f	-		143	-			
Reverse bias safe operating area	RBSOA	T _J = 150 °C, I _C = 150 A, R _g = 22 Ω, V _{GE} = 15 V to 0 V, V _{CC} = 900 V, V _P = 1200 V		Fullsquare				
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _R = 200 V		-	129	161	ns	
Diode peak reverse current	I _{rr}			-	11	14	A	
Diode recovery charge	Q _{rr}			-	700	1046	nC	
Diode reverse recovery time	t _{rr}	I _F = 50 A, dI _F /dt = 200 A/μs, V _R = 200 V, T _J = 125 °C		-	208	257	ns	
Diode peak reverse current	I _{rr}			-	17	21	A	
Diode recovery charge	Q _{rr}			-	1768	2698	nC	



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL		MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J, T_{Stg}		- 40	-	150	°C
Junction to case	R_{thJC}	IGBT	-	-	0.29	°C/W
		Diode	-	-	0.45	
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	-	1.3	Nm
Case style	SOT-227					

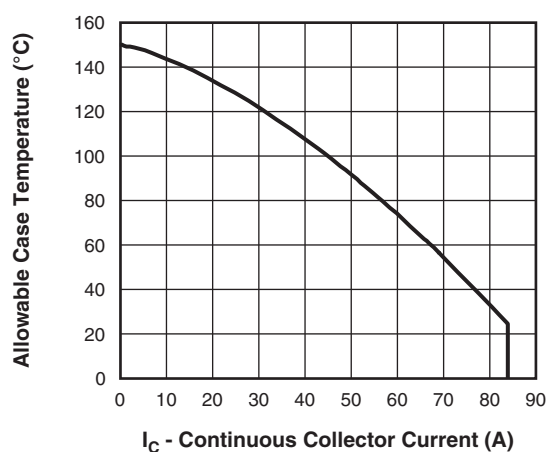


Fig. 1 - Maximum DC IGBT Collector Current vs. Case Temperature

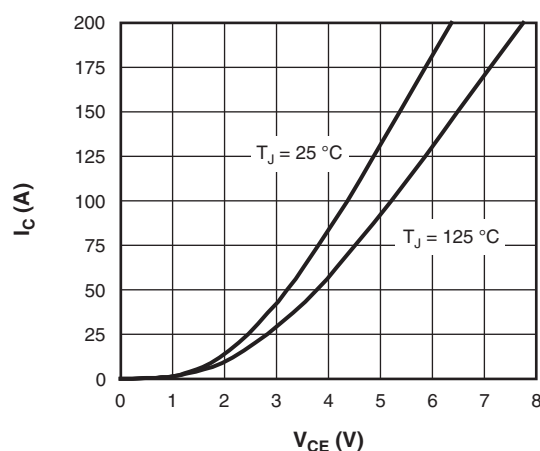


Fig. 3 - Typical IGBT Collector Current Characteristics

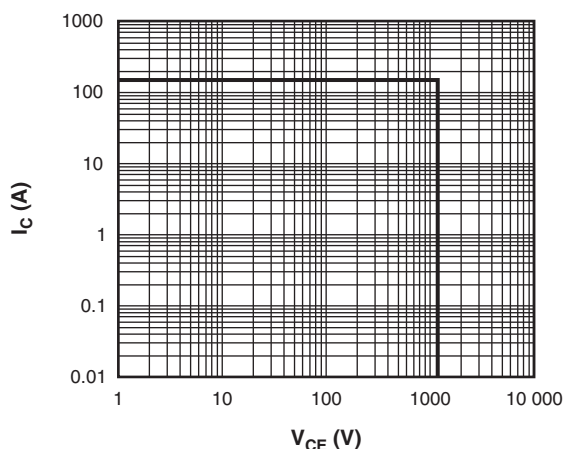


Fig. 2 - IGBT Reverse Bias SOA
 $T_J = 150\text{ °C}$, $V_{GE} = 15\text{ V}$

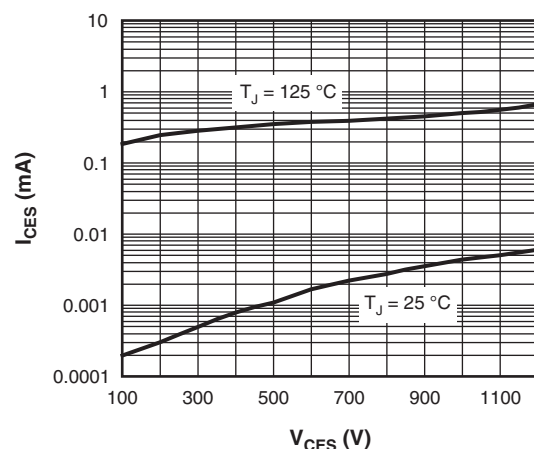


Fig. 4 - Typical IGBT Zero Gate Voltage Collector Current

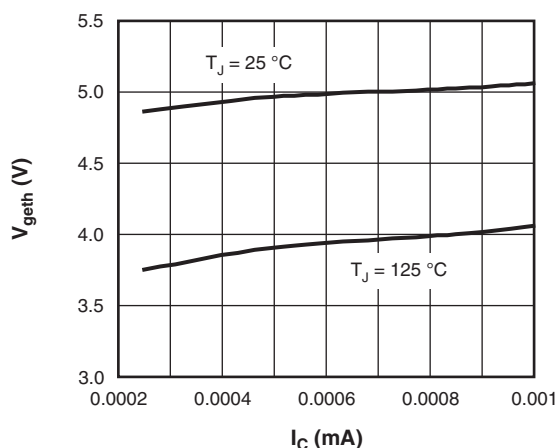


Fig. 5 - Typical IGBT Threshold Voltage

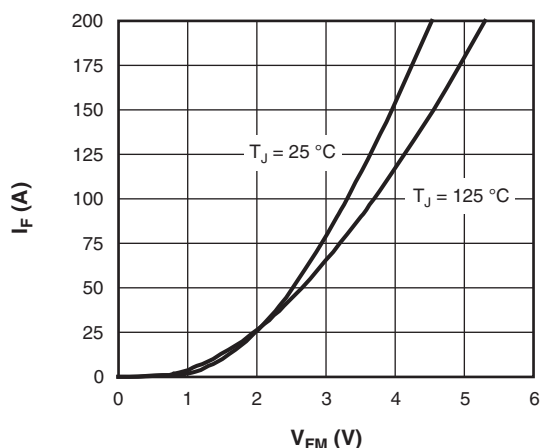


Fig. 8 - Typical Diode Forward Characteristics

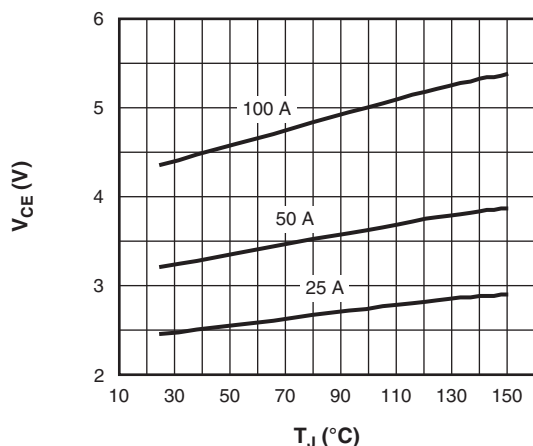
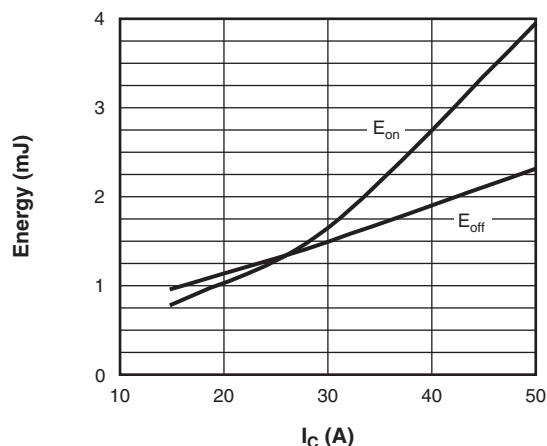
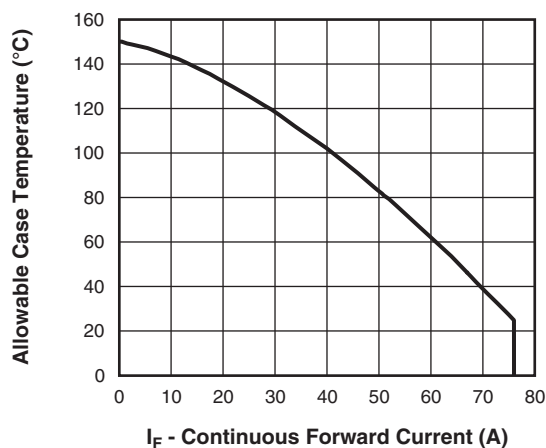
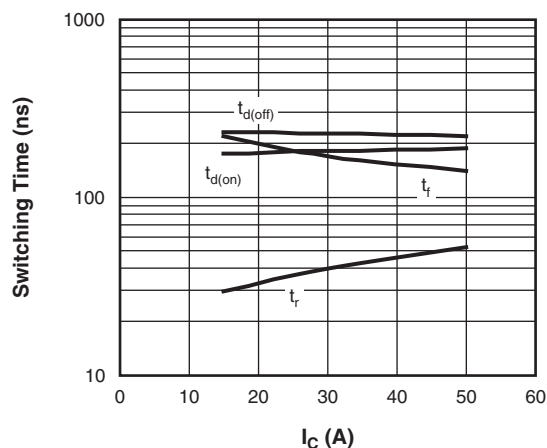

Fig. 6 - Typical IGBT Collector to Emitter Voltage vs. Junction Temperature, $V_{GE} = 15\text{ V}$

Fig. 9 - Typical IGBT Energy Loss vs. I_c
 $T_J = 125\text{ °C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 600\text{ V}$,
 $R_g = 5\text{ }\Omega$, $V_{GE} = 15\text{ V}$


Fig. 7 - Maximum DC Forward Current vs. Case Temperature


Fig. 10 - Typical IGBT Switching Time vs. I_c
 $T_J = 125\text{ °C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 600\text{ V}$,
 $R_g = 5\text{ }\Omega$, $V_{GE} = 15\text{ V}$

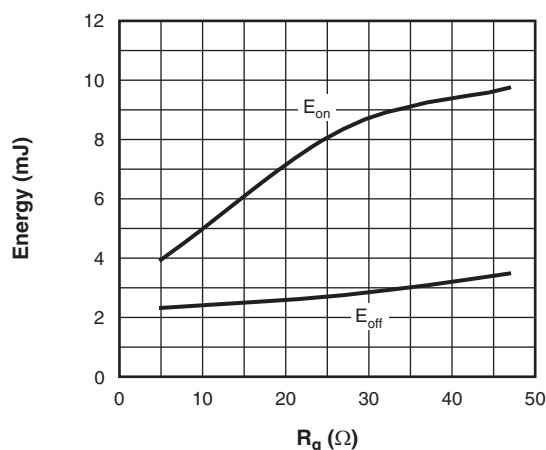


Fig. 11 - Typical IGBT Energy Loss vs. R_g
 $T_J = 125^\circ\text{C}$, $I_C = 50\text{ A}$, $L = 500\text{ }\mu\text{H}$,
 $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$

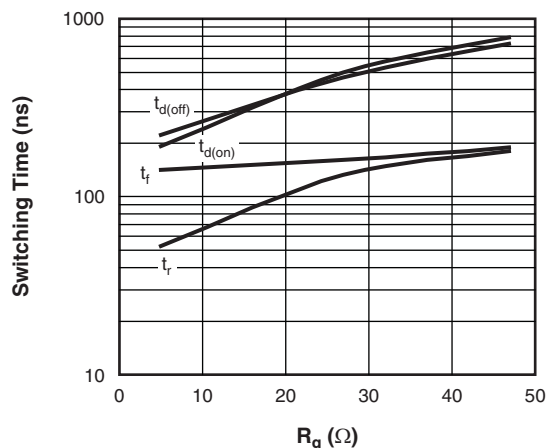


Fig. 12 - Typical IGBT Switching Time vs. R_g
 $T_J = 125^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CC} = 600\text{ V}$,
 $I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$

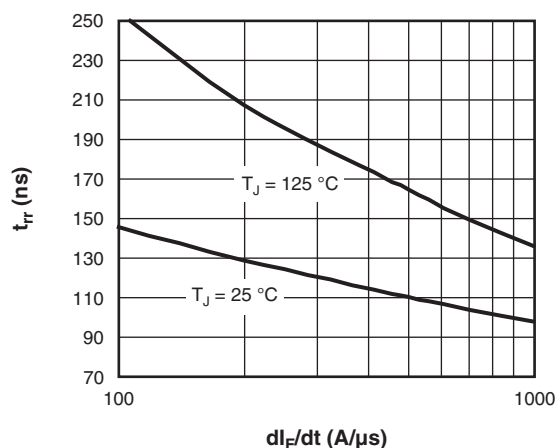


Fig. 13 - Typical t_{rr} Diode vs. dI_F/dt
 $V_R = 200\text{ V}$, $I_F = 50\text{ A}$

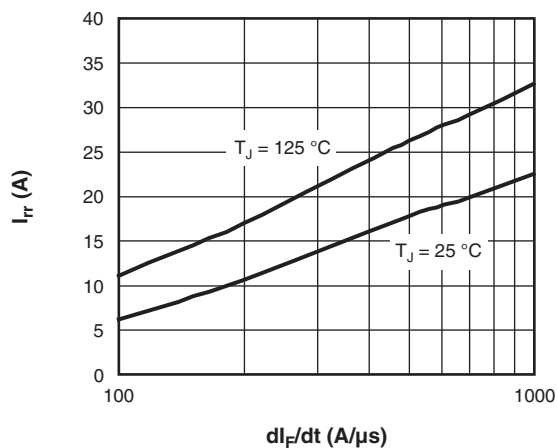


Fig. 14 - Typical I_{rr} Diode vs. dI_F/dt
 $V_R = 200\text{ V}$, $I_F = 50\text{ A}$

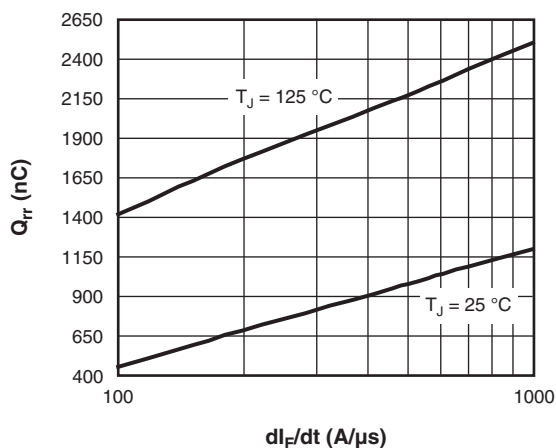


Fig. 15 - Typical Q_{rr} Diode vs. dI_F/dt , $V_R = 200\text{ V}$, $I_F = 50\text{ A}$

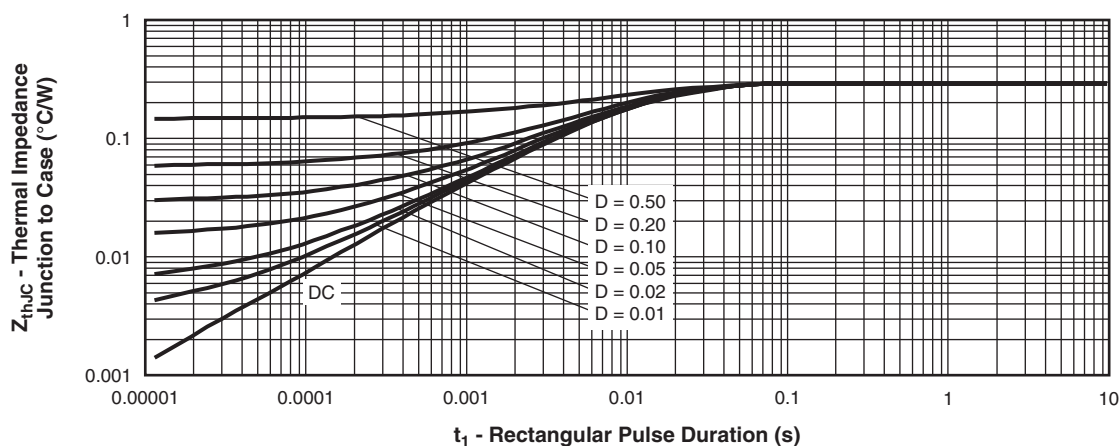


Fig. 16 - Maximum Thermal Impedance Z_{thJC} Characteristics (IGBT)

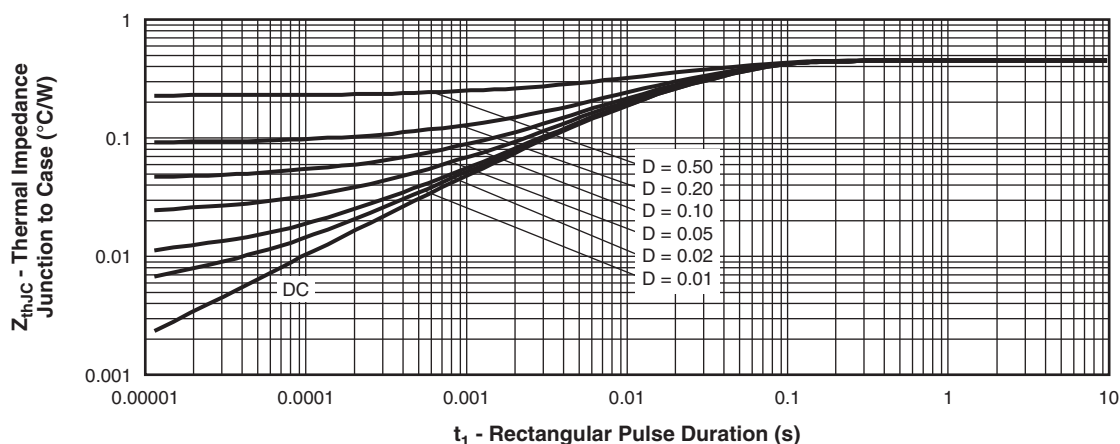


Fig. 17 - Maximum Thermal Impedance Z_{thJC} Characteristics (Diode)

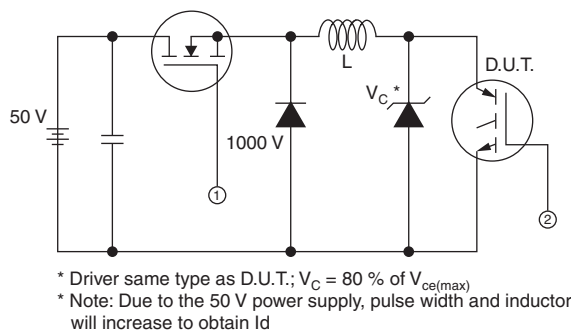


Fig. 18a - Clamped Inductive Load Test Circuit

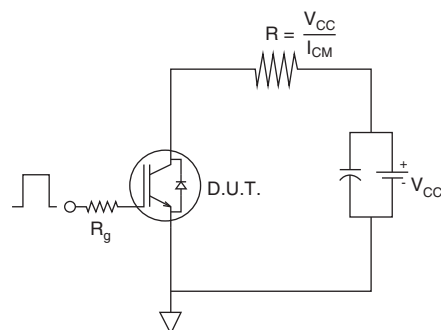


Fig. 18b - Pulsed Collector Current Test Circuit

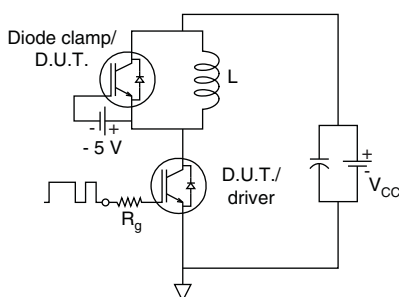


Fig. 19a - Switching Loss Test Circuit

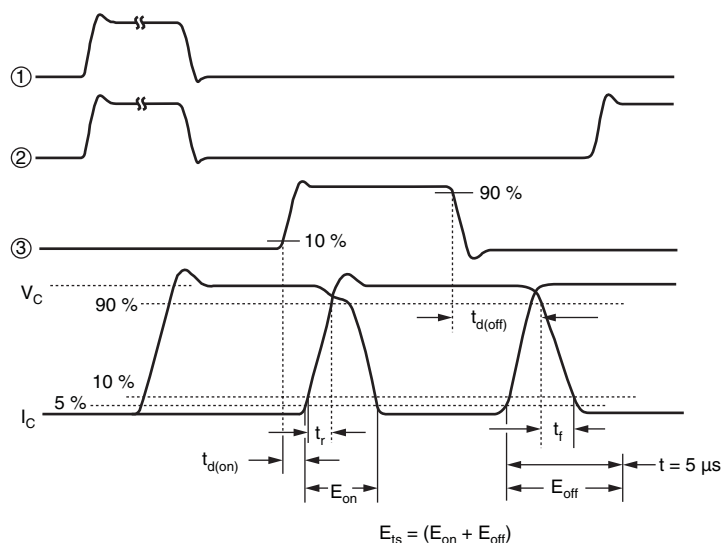
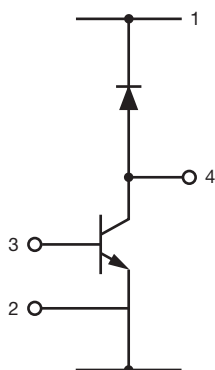


Fig. 19b - Switching Loss Waveforms Test Circuit

ORDERING INFORMATION TABLE

Device code	VS-	G	B	50	L	A	120	U	X
	1	2	3	4	5	6	7	8	9

- | | | |
|----------|---|--|
| 1 | - | Vishay Semiconductors product |
| 2 | - | Insulated Gate Bipolar Transistor (IGBT) |
| 3 | - | B = IGBT Generation 5 |
| 4 | - | Current rating (50 = 50 A) |
| 5 | - | Circuit configuration (L = Low side chopper) |
| 6 | - | Package indicator (A = SOT-227) |
| 7 | - | Voltage rating (120 = 1200 V) |
| 8 | - | Speed/type (U = Ultrafast IGBT) |
| 9 | - | X = F/W HEXFRED® diode |

CIRCUIT CONFIGURATION


LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95036
Packaging information	www.vishay.com/doc?95037

DIMENSIONS in millimeters (inches)



- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



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